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JAN - 9 2003

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

TC 2800 MAIL ROOM

Applicants: Schroeder et al.

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Examiner: Nadav, O.

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Application No.: 09/389,826

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Art Unit: 2811

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Filed: 09/03/1999

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For: SEMICONDUCTOR DEVICE

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Box Non-Fee Amendment
Commissioner for Patents
Washington D.C. 20231

AFTER-FINAL AMENDMENT

Sir:

In response to the Final Office Action of October 1, 2002, Applicants hereby respond as follows:

In the Specification

Please amend the paragraph starting on page 5, line 13 as follows:

Fig. 4 shows a plan view of an ESD protection according to the invention having another layout compared with the previous example. Cross-sections of the device along the lines V-V and VI-VI are represented in Fig. 5, Fig. 6 respectively. The n-type well 11 is arranged in the form of a longitudinal zone having two ends on the left and right-hand side of the drawing. The anode 8 is formed by a longitudinal p-type zone in the n-well 11 which well has in its center an opening at the position of which a highly doped n-type zone 12 is provided which forms a

Serial No.: 09/389,826

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